华润微电子(重庆)有限公司

CRJQ190N65GCF

SJMOS N-MOSFET 650V, 185mΩ, 23A

Features

- CRM(CQ) Super_Junction technology
- Much lower Ron*A performance for On-state efficiency
- Much lower FOM for fast switching efficiency

Product Summary

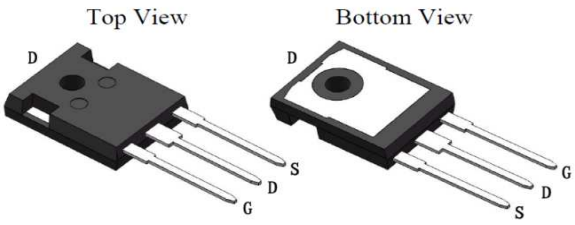
VDS	650V
$R_{DS(on)\_typ}$	185mΩ
I_D	23A

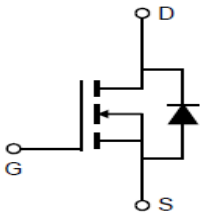
Applications

- LED/LCD/PDP TV and monitor Lighting
- Solar/Renewable/UPS-Micro Inverter System
- Charger
- Power Supply

100% DVDS Tested

100% Avalanche Tested





Package Marking and Ordering Information

Part #	Marking	Package	Packing	Reel Size	Tape Width	Qty
CRJQ190N65GCF	-	TO-247-3L	Tube	N/A	N/A	25/30pcs

Absolute Maximum Ratings(at Tj = 25 °C, unless otherwise specified)

Parameter	Symbol	Value	Unit
Drain-source voltage	V_{DS}	650	V
Continuous drain current T_C = 25°C T_C = 100°C	I_D	 23 14.8	A
Pulsed drain current (T_C = 25°C, t_p limited by T_{jmax})	$I_{D\ pulse}$	93	A
Avalanche energy, single pulse (L=30mH, ID=3.9A, VDD=50V)	E_{AS}	220	mJ
Gate-Source voltage	V_{GS}	±30	V
Power dissipation (T_C = 25°C)	P_{tot}	229	W
Operating junction and storage temperature	T_j , T_{stg}	-55...+150	°C
Continuous diode forward current(T_C = 25°C)	I_S	23	A
Diode pulse current(T_C = 25°C)	$I_{S\ pulse}$	93	A

Thermal Resistance

Parameter	Symbol	Value	Unit
Thermal resistance, junction – case. Max	R_{thJC}	0.55	°C/W
Thermal resistance, junction – ambient. Max	R_{thJA}	45	

Electrical Characteristic (at Tj = 25 °C, unless otherwise specified)

Parameter	Symbol	Value			Unit	Test Condition
		min.	typ.	max.		
Static Characteristic						
Drain-source breakdown voltage	BV_{DSS}	650	-	-	V	V_{GS}=0V, I_D=250uA
Gate threshold voltage	$V_{GS(th)}$	3.2		4.6	V	V_{DS}=V_{GS},I_D=250uA
Zero gate voltage drain current	I_{DSS}	- -	- 1000	5 -	μA	V_{DS}=650V,V_{GS}=0V T_j=25°C T_j=150°C
Gate-source leakage current	I_{GSS}	-		±100	nA	V_{GS}=±30V, V_{DS}=0V
Drain-source on-state resistance	$R_{DS(on)}$	- -	185 518	210 -	mΩ	V_{GS}=10V, I_D=10A, T_j=25°C T_j=150°C
Transconductance	g_{fs}	-	14.5	-	S	V_{DS}=20V,I_D=10A
Dynamic Characteristic						
Input Capacitance	C_{iss}	-	1427	-	pF	V_{GS}=0V, V_{DS}=100V, f=1MHz
Output Capacitance	C_{oss}	-	67	-		
Reverse Transfer Capacitance	C_{rss}	-	21	-		
Gate Total Charge	Q_G	-	41	-	nC	V_{GS}=10V, V_{DS}=480V, I_D=10A
Gate-Source charge	Q_{gs}	-	12	-		
Gate-Drain charge	Q_{gd}	-	20	-		
Turn-on delay time	$t_{d(on)}$	-	42.5	-	ns	V_{GS}=10V, I_D=10A, V_{DS}=325V, R_g=10Ω
Rise time	t_r	-	58	-		
Turn-off delay time	$t_{d(off)}$	-	105	-		
Fall time	t_f	-	36	-		
Gate resistance	Rgint	-	0.9	-	Ω	f=1MHz

Body Diode Characteristic

Parameter	Symbol	Value			Unit	Test Condition
		min.	typ.	max.		
Body Diode Forward Voltage	V_{SD}	0.5	0.84	1	V	V_{GS}=0V,I_{SD}=10A
Body Diode Reverse Recovery Time	t_{rr}	-	108	-	ns	Isd=10A dI/dt=100A/us,Vds=100 V
Body Diode Reverse Recovery Charge	Q_{rr}	-	0.54	-	uC	
Body Diode Reverse Recovery Peak Current	I_{rrm}	-	9.8	-	A	

Typical Performance Characteristics

Fig 1. Output Characteristics (Tj=25℃)

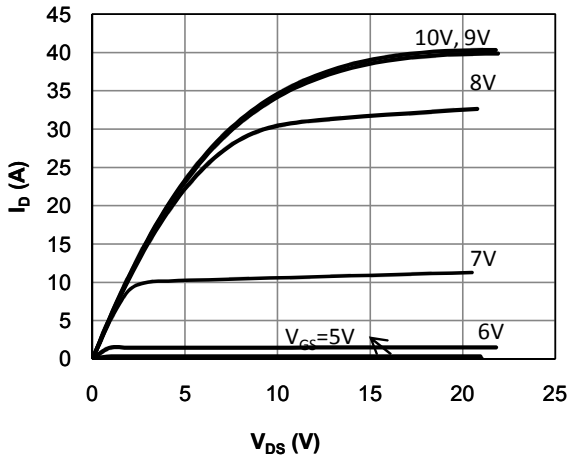


Fig 2. Output Characteristics (Tj=150℃)

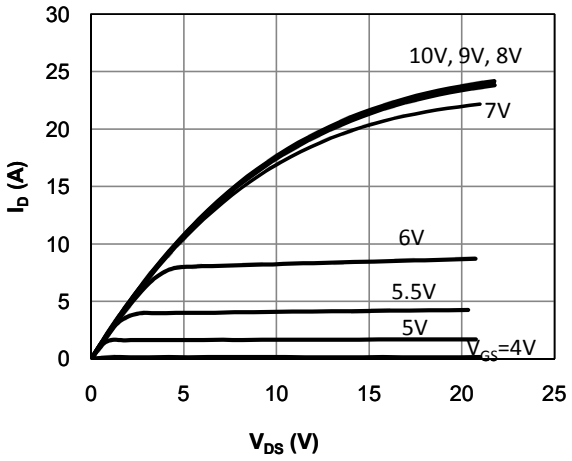


Fig 3: Transfer Characteristics

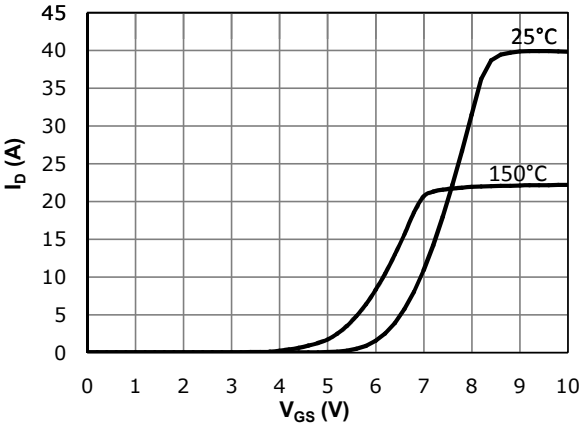


Fig 4: V_{TH} Vs Tj Temperature Characteristics

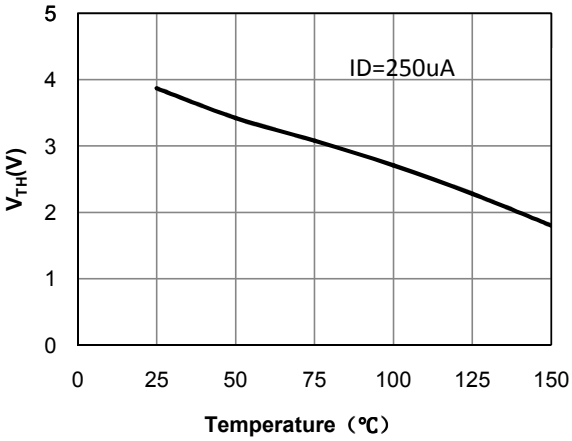


Fig 5: Rdson Vs Ids Characteristics(Tj=25℃)

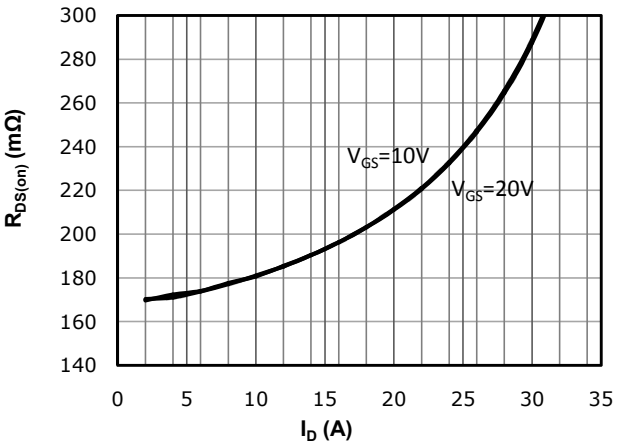


Fig 6: Rds(on) vs. Temperature

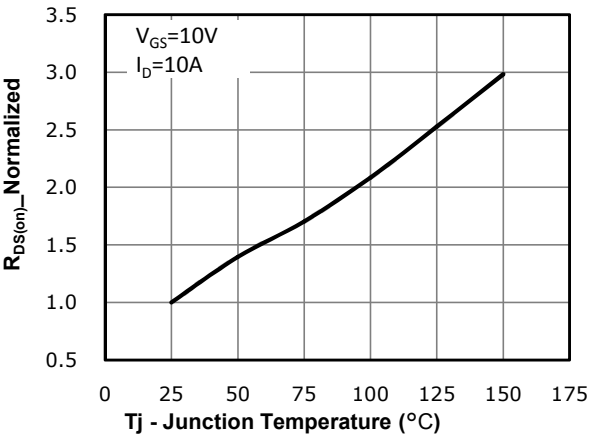


Fig 7: BVDSS vs. Temperature

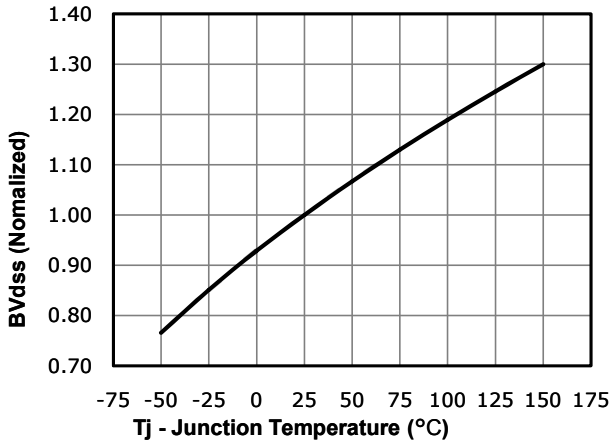


Fig 8: Rds(on) vs Gate Voltage

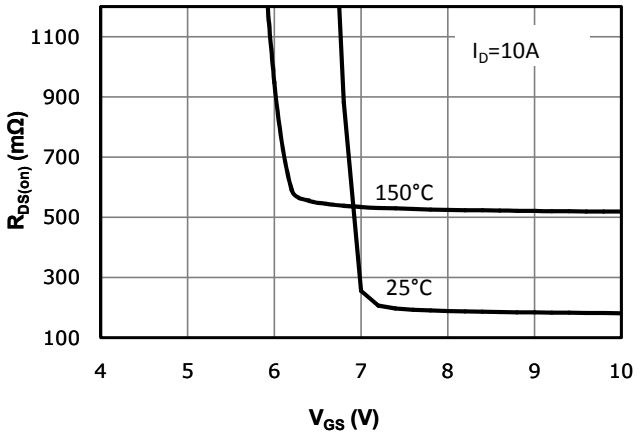


Fig 9: Body-diode Forward Characteristics

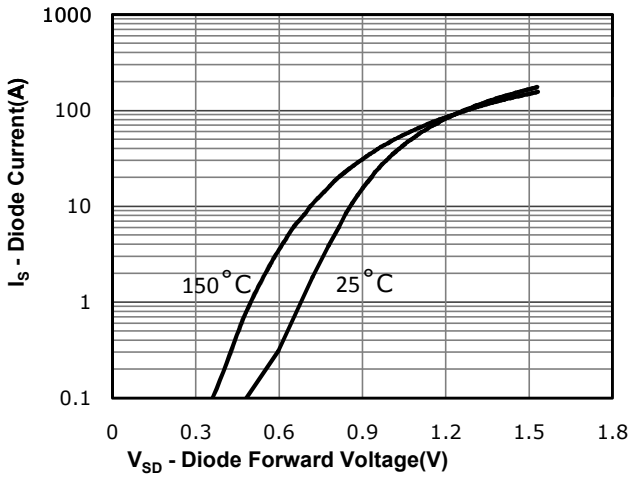


Fig 10: Gate Charge Characteristics

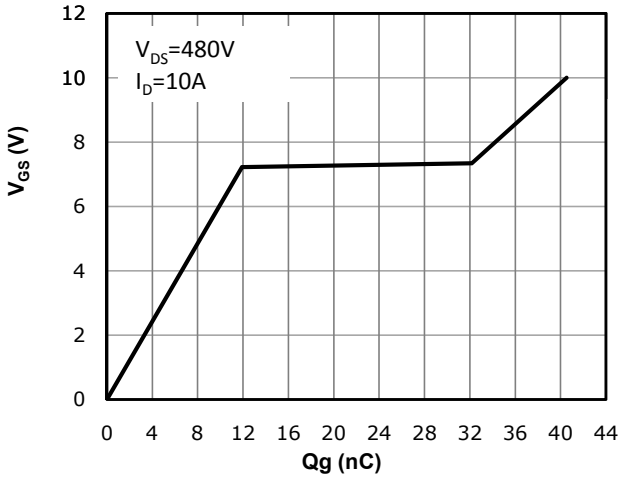


Fig 11: Capacitance Characteristics

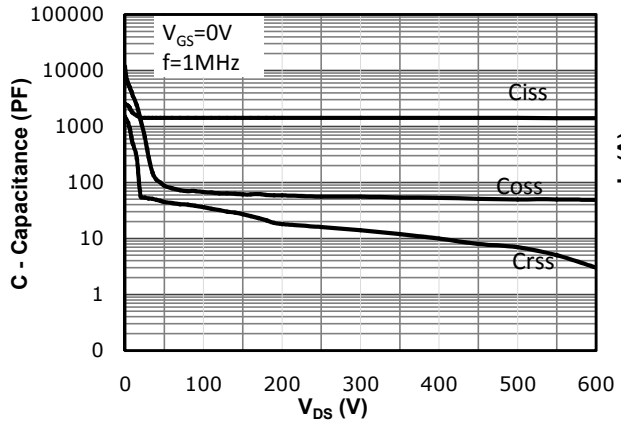


Fig 12: Safe Operating Area

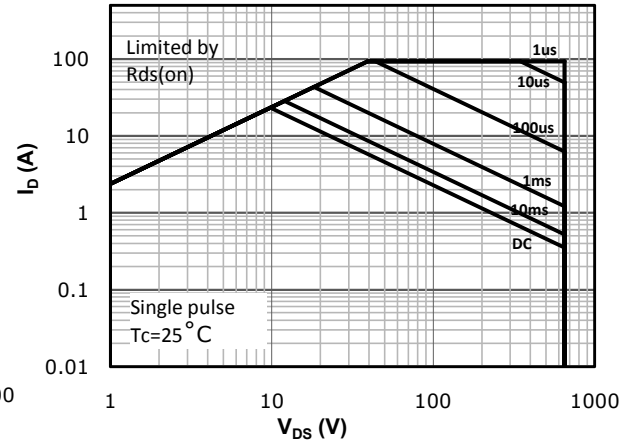
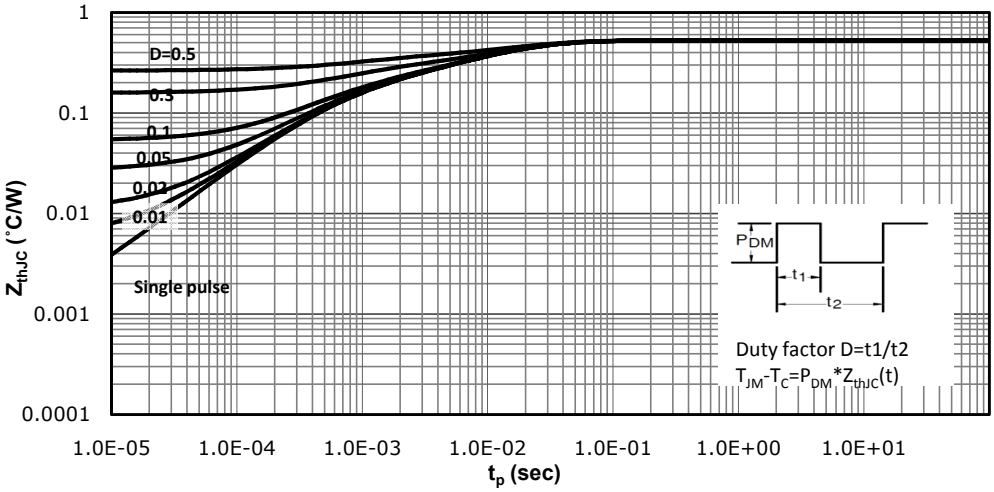
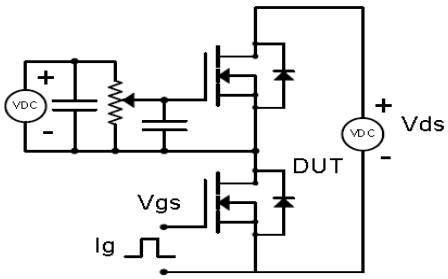


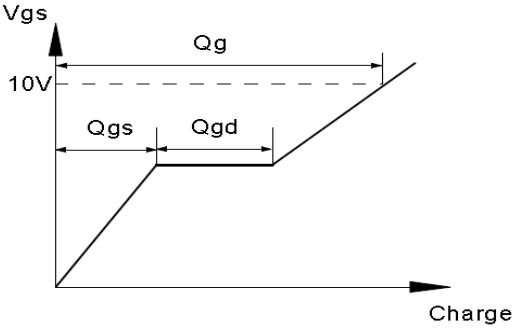
Fig 13: Max. Transient Thermal Impedance



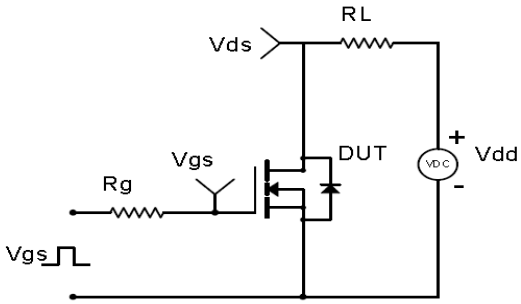
Test Circuit & Waveform

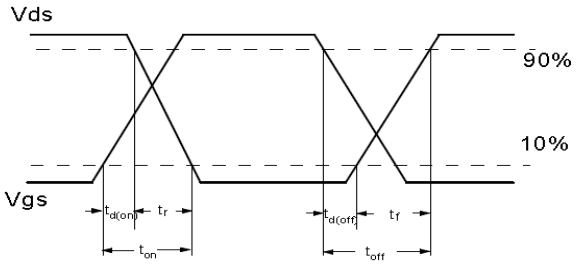
Gate Charge Test Circuit & Waveform



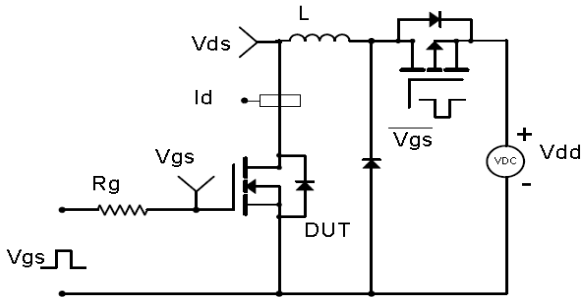


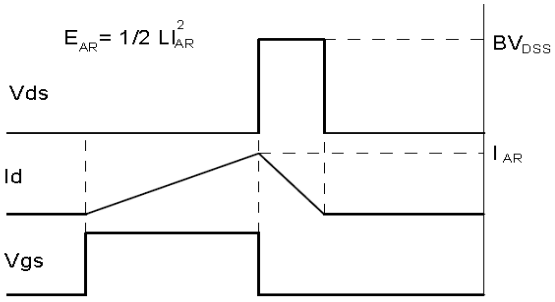
Resistive Switching Test Circuit & Waveforms



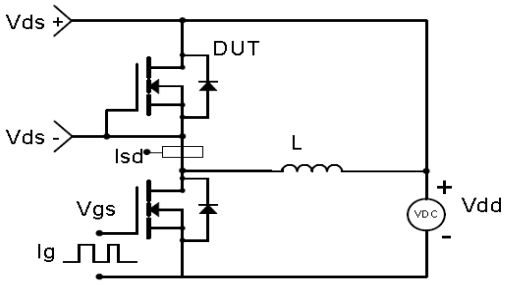


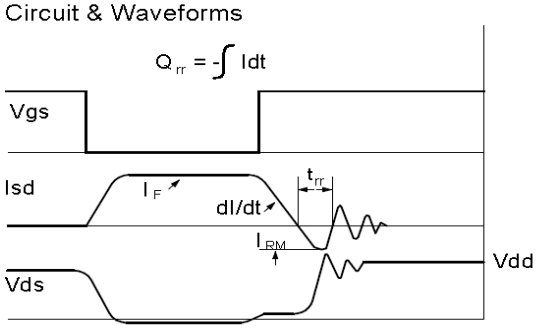
Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



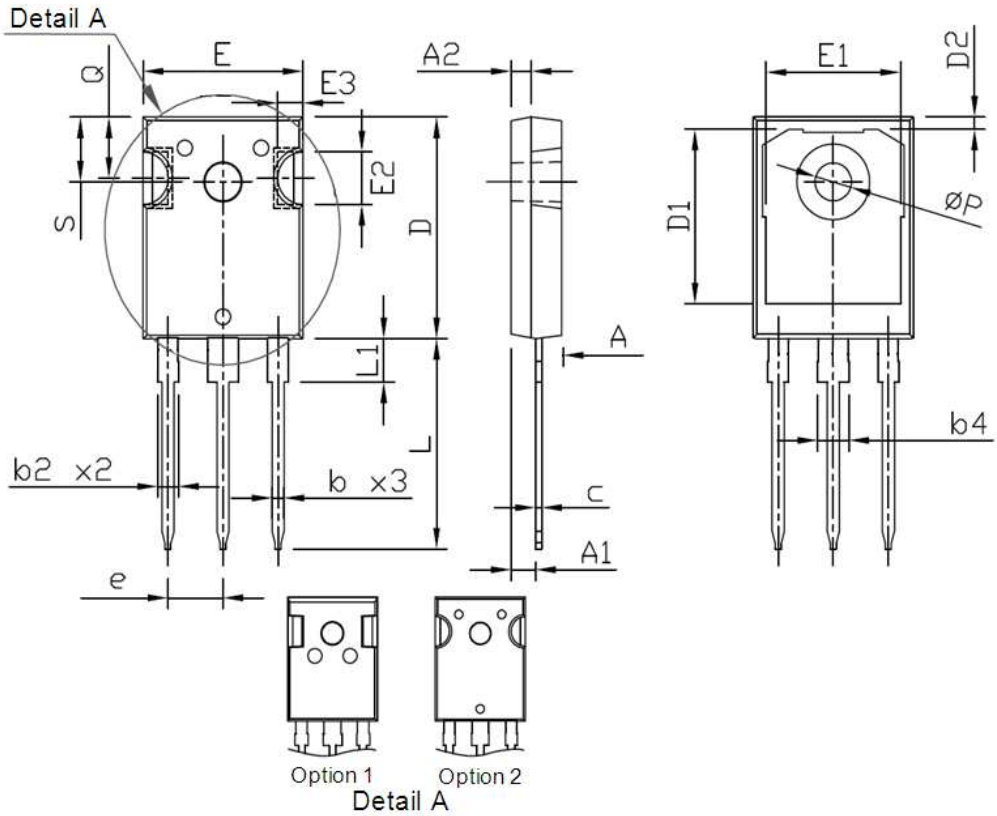


Diode Recovery Test Circuit & Waveforms





Package Outline: TO-247



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	4.70	5.30	0.185	0.209
A1	2.20	2.60	0.087	0.102
A2	1.50	2.49	0.059	0.098
b	1.04	1.33	0.041	0.052
b2	1.90	2.41	0.075	0.095
b4	2.87	3.43	0.113	0.135
c	0.55	0.70	0.022	0.028
D	20.70	21.30	0.815	0.839
D1	16.25	17.65	0.640	0.695
D2	0.51	1.40	0.020	0.055
e	5.44 BSC.		0.214 BSC.	
E	15.50	16.30	0.610	0.642
E1	13.08	14.16	0.515	0.557
E2	3.80	5.49	0.150	0.216
E3	1.00	2.75	0.039	0.108
L	19.72	20.32	0.776	0.800
L1	3.85	4.50	0.152	0.177
Q	5.25	6.25	0.207	0.246
P	3.50	3.70	0.138	0.146
S	6.04	6.30	0.238	0.248

Revision History

Revison	Date	Major changes
1.2	2021-12-15	Update Package Marking and Ordering Information

Disclaimer

Unless otherwise specified in the datasheet, the product is designed and qulified as a standard commercial product and is not intended for use in applications that require extraordinary levels of quality and reliability, such as automotive, aviation/aerospace and life-support devices or systems.

Any and all semicondutor products have certain probability to fail or malfunction, which may result in personal injury, death or property damage. Customer are solely responsible for providing adequate safe measures when design their systems.

CRM(CQ) reserves the right to improve product design, function and reliability without notice.